

EXHIBIT

USSN 10/017,325

Ohba Fig. 6

Active layers 12 - 16
AlN (Ga) layer 11 (0.03 - 0.5 μm)
Substrate 10 (Sapphire)

Ogawa Fig. 1

Active layers
GaN, AlN or Ga AlN layer 104 (3 μm)
GaN 103 (20 nm = 0.02 μm)
Substrate 102 (GaN)

* Opposite to what is stated in 1st paragraph on page 3 of the Office Action

Pending Claim 1

Active layers
2nd nitride (0.002 - 0.1 μm)
Al - including 1st nitride (0.5 - 1000 μm)
Substrate